BLS6G2735L-30; BLS6G2735LS-30 S-band LDMOS transistor Rev. 4 — 1 September 2015

AMPLEON

Product data sheet

Product profile

1.1 General description

30 W LDMOS power transistor for S-band radar applications in the frequency range from 2.7 GHz to 3.5 GHz.

Application information Table 1.

Typical RF performance at T_{case} = 25 °C; t_{D} = 300 μ s; δ = 10 %; I_{Dq} = 50 mA.

Test signal	f	V _{DS}	PL	^			
			FL	G_p	η_{D}	t _r	t _f
	(GHz)	(V)	(W)	(dB)	(%)	(ns)	(ns)
Typical RF performance	Typical RF performance in a class-AB production test circuit in band 3.1 GHz to 3.5 GHz						5 GHz
pulsed RF	3.1 to 3.5	32	30	13	50	20	10
Typical RF performance	in an applic	ation circ	uit in sm	all band 2	.7 GHz to	3.3 GHz	
pulsed RF	2.7 to 3.3	32	35	14	50	20	10
Typical RF performance in an application circuit in small band 2.7 GHz to 3.5 GHz							
pulsed RF	2.7 to 3.5	32	30	12	47	20	10

1.2 Features and benefits

- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (2.7 GHz to 3.5 GHz)
- Internally matched for ease of use
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

S-band radar applications in the frequency range 2.7 GHz to 3.5 GHz

3 sym112

2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
BLS6G273	5L-30 (SOT1135A)			
1	drain			,
2	gate		1	1
3	source	[1]		2 3 sym112
BLS6G273	5LS-30 (SOT1135B)			
1	drain		-	,
2	gate		1	ئے.
3	source	<u>[1]</u>		ا ا

3. Ordering information

Table 3. Ordering information

Type number	Packag	ckage				
	Name	Description	Version			
BLS6G2735L-30	-	flanged ceramic package; 2 mounting holes; 2 leads	SOT1135A			
BLS6G2735LS-30	-	earless flanged ceramic package; 2 leads	SOT1135B			

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Min	Max	Unit
V_{DS}	drain-source voltage	-	60	V
V_{GS}	gate-source voltage	-0.5	+13	V
T _{stg}	storage temperature	-65	+150	°C
Tj	junction temperature	-	225	°C

^[1] Connected to flange.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$Z_{\text{th(j-c)}} \qquad \text{transient thermal impedance from junction} \\ \text{to case}$	transient thermal impedance from junction	$T_h = 85 ^{\circ}C; P_{L(CW)} = 30 W$		
	t_p = 100 μ s; δ = 10 %	0.507	K/W	
		t_p = 200 μ s; δ = 10 %	0.662	K/W
		t_p = 300 μ s; δ = 10 %	0.761	K/W
		t_p = 100 μ s; δ = 20 %	0.594	K/W

6. Characteristics

Table 6. DC characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.5 \text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_{D} = 40 mA	1.4	2	2.4	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V	-	-	1.4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	8.2	-	Α
I_{GSS}	gate leakage current	V_{GS} = 8.3 V; V_{DS} = 0 V	-	-	140	nA
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 1.4 A	-	2.8	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 1.4 \text{ A}$	-	0.37	0.58	Ω

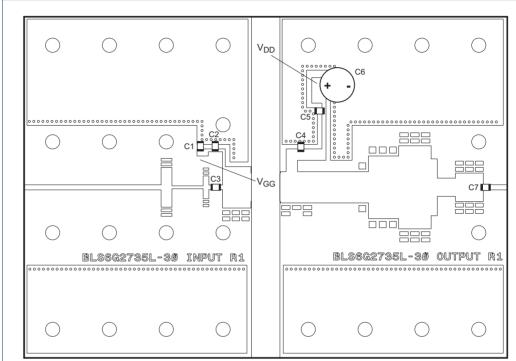
Table 7. RF characteristics

Test signal: pulsed RF; f_1 = 3100 MHz; f_2 = 3300 MHz; f_3 = 3500 MHz; t_p = 300 μ s; δ = 10 %; V_{DS} = 32 V; I_{Dq} = 50 mA; T_{case} = 25 °C; unless otherwise specified, in the class-AB RF production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
P_L	output power		-	30	-	W
Gp	power gain	P _L = 30 W	11	13	-	dB
η_{D}	drain efficiency	P _L = 30 W	43	50	-	%
t _r	rise time	P _L = 30 W	-	20	50	ns
t _f	fall time	P _L = 30 W	-	10	50	ns

7. Application information

7.1 Circuit information for application circuit (2.7 GHz to 3.5 GHz)



aaa-001308

Printed-Circuit Board (PCB): Rogers 3006; ϵ_{r} = 6.15; thickness = 0.64 mm; thickness copper plating = 35 μm .

See Table 8 for a list of components.

Fig 1. Component layout for RF test circuit

Table 8. List of components

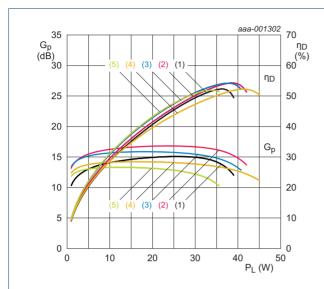
For test circuit see Figure 1.

Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	$2~\mu\text{F},50~\text{V}$	<u>[1]</u>
C2	multilayer ceramic chip capacitor	100 pF	[2]
C3	multilayer ceramic chip capacitor	0.6 pF	[2]
C4, C7	multilayer ceramic chip capacitor	10 pF	[2]
C5	multilayer ceramic chip capacitor	1 μF, 50 V	<u>[1]</u>
C6	electrolytic capacitor	470 μF, 63 V	

^[1] TDK or capacitor of same quality.

[2] American Technical Ceramics type 800A or capacitor of same quality.

7.2 Measured in application circuit from 2.7 GHz to 3.5 GHz



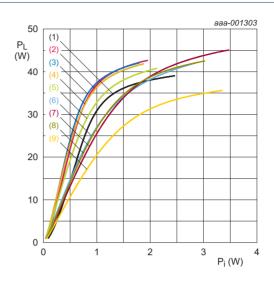
 V_{DS} = 32 V; I_{Dq} = 50 mA; t_p = 300 μ s; δ = 10 %

output power; typical values

- (1) f = 2700 MHz
- (2) f = 2900 MHz
- (3) f = 3100 MHz
- (4) f = 3300 MHz
- (5) f = 3500 MHz

Fig 2.

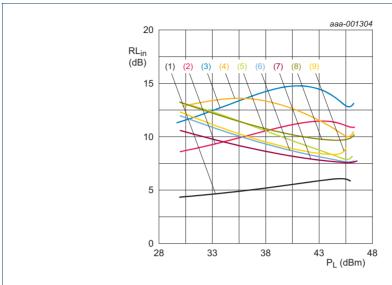
Power gain and drain efficiency as function of



 V_{DS} = 32 V; I_{Dq} = 50 mA; t_p = 300 $\mu s; \, \delta$ = 10 %

- (1) f = 2700 MHz
- (2) f = 2800 MHz
- (3) f = 2900 MHz
- (4) f = 3000 MHz
- (5) f = 3100 MHz
- (6) f = 3200 MHz(7) f = 3300 MHz
- (8) f = 3400 MHz
- (9) f = 3500 MHz

Fig 3. Output power as a function of input power; typical values

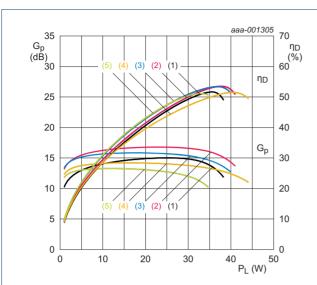


 V_{DS} = 32 V; I_{Dq} = 50 mA; t_p = 300 μ s; δ = 10 %

- (1) f = 2700 MHz
- (2) f = 2800 MHz
- (3) f = 2900 MHz
- (4) f = 3000 MHz
- (5) f = 3100 MHz
- (6) f = 3200 MHz
- (7) f = 3300 MHz
- (8) f = 3400 MHz
- (9) f = 3500 MHz

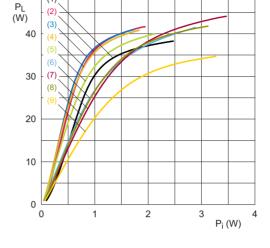
Fig 4. Input return loss as a function of output power; typical values

aaa-001306



 V_{DS} = 32 V; I_{Dq} = 50 mA; t_p = 100 μ s; δ = 20 %

- (1) f = 2700 MHz
- (2) f = 2900 MHz
- (3) f = 3100 MHz
- (4) f = 3300 MHz
- (5) f = 3500 MHz

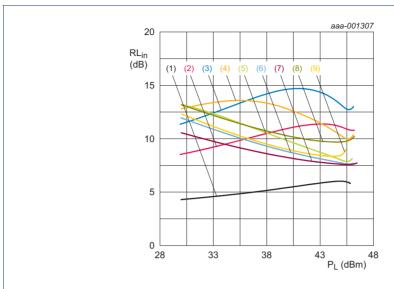


 V_{DS} = 32 V; I_{Dq} = 50 mA; t_p = 100 $\mu s; \, \delta$ = 20 %

- (1) f = 2700 MHz
- (2) f = 2800 MHz
- (3) f = 2900 MHz
- (4) f = 3000 MHz
- (5) f = 3100 MHz
- (6) f = 3200 MHz
- (7) f = 3300 MHz(8) f = 3400 MHz
- (9) f = 3500 MHz

Fig 6. Output power as a function of input power; typical values

Fig 5. Power gain and drain efficiency as function of output power; typical values



 V_{DS} = 32 V; I_{Dq} = 50 mA; t_p = 100 $\mu s; \, \delta$ = 20 %

- (1) f = 2700 MHz
- (2) f = 2800 MHz
- (3) f = 2900 MHz
- (4) f = 3000 MHz
- (5) f = 3100 MHz
- (6) f = 3200 MHz
- (7) f = 3300 MHz
- (8) f = 3400 MHz
- (9) f = 3500 MHz

Fig 7. Input return loss as a function of output power; typical values

8. Test information

8.1 Ruggedness in class-AB operation

The BLS6G2735L-30 and BLS6G2735LS-30 are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 32 V; I_{Dq} = 50 mA; P_L = 30 W; t_p = 300 μ s; δ = 10 %.

8.2 Impedance information

Table 9. Typical impedance

Source and load impedances obtained in a wideband test circuit.

f	Z _S	Z _L
GHz	Ω	Ω
2.7	3.4 – j16.0	32.7 – j3.8
2.9	4.3 – j13.0	20.3 – j4.2
3.1	5.4 – j11.6	18.3 – j3.9
3.3	5.4 – j12.0	15.0 – j7.2
3.5	3.7 – j11.7	8.4 – j6.6

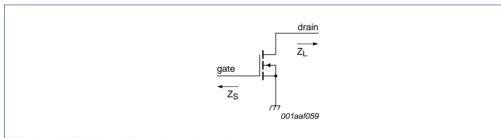
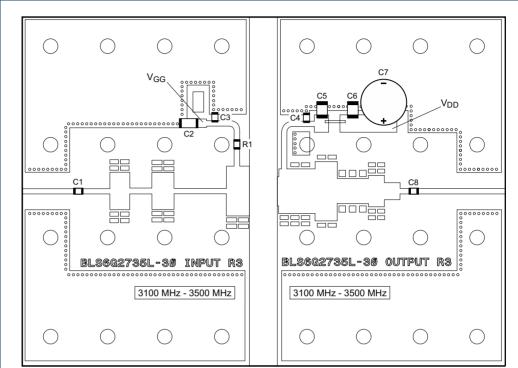


Fig 8. Definition of transistor impedance

8.3 Circuit information for production test circuit (3.1 GHz to 3.5 GHz)



aaa-004510

Printed-Circuit Board (PCB): Rogers Duroid 6006; ϵ_r = 6.15; thickness = 0.64 mm; thickness copper plating = 35 μ m.

See Table 10 for a list of components.

Fig 9. Component layout for RF production test circuit

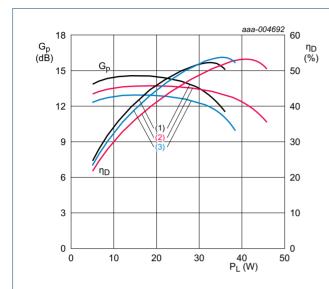
Table 10. List of components For test circuit see Figure 9.

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Component	Description	Value	Remarks		
C1, C3, C4, C8	multilayer ceramic chip capacitor	10 pF	<u>[1]</u>		
C2	multilayer ceramic chip capacitor	1 μF	[2]		
C5	multilayer ceramic chip capacitor	4.7 μF, 50 V	[2]		
C6	multilayer ceramic chip capacitor	10 μF, 50 V	[2]		
C7	electrolytic capacitor	100 μF, 63 V			
R1	SMD resistor	10 Ω			

^[1] American Technical Ceramics type 800A or capacitor of same quality.

^[2] TDK or capacitor of same quality.

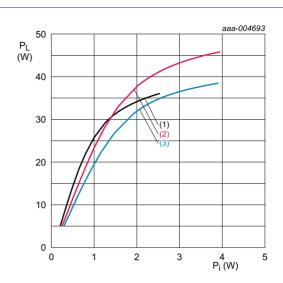
8.4 Measured in RF production test circuit from 3.1 GHz to 3.5 GHz



 V_{DS} = 32 V; I_{Dq} = 50 mA; t_p = 300 μ s; δ = 10 %

- (1) f = 3100 MHz
- (2) f = 3300 MHz
- (3) f = 3500 MHz

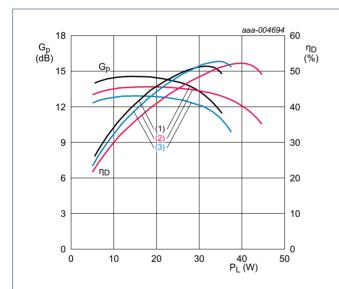
Fig 10. Power gain and drain efficiency as function of output power; typical values



 V_{DS} = 32 V; I_{Dq} = 50 mA; t_p = 300 μ s; δ = 10 %

- (1) f = 3100 MHz
- (2) f = 3300 MHz
- (3) f = 3500 MHz

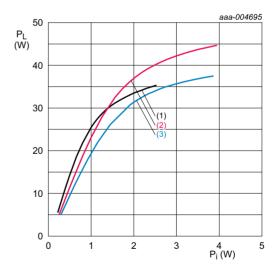
Fig 11. Output power as a function of input power; typical values



 V_{DS} = 32 V; I_{Dq} = 50 mA; t_p = 100 μ s; δ = 20 %

- (1) f = 3100 MHz
- (2) f = 3300 MHz
- (3) f = 3500 MHz

Fig 12. Power gain and drain efficiency as function of output power; typical values



 V_{DS} = 32 V; I_{Dq} = 50 mA; t_p = 100 μ s; δ = 20 %

- (1) f = 3100 MHz
- (2) f = 3300 MHz
- (3) f = 3500 MHz

Fig 13. Output power as a function of input power; typical values

9. Package outline

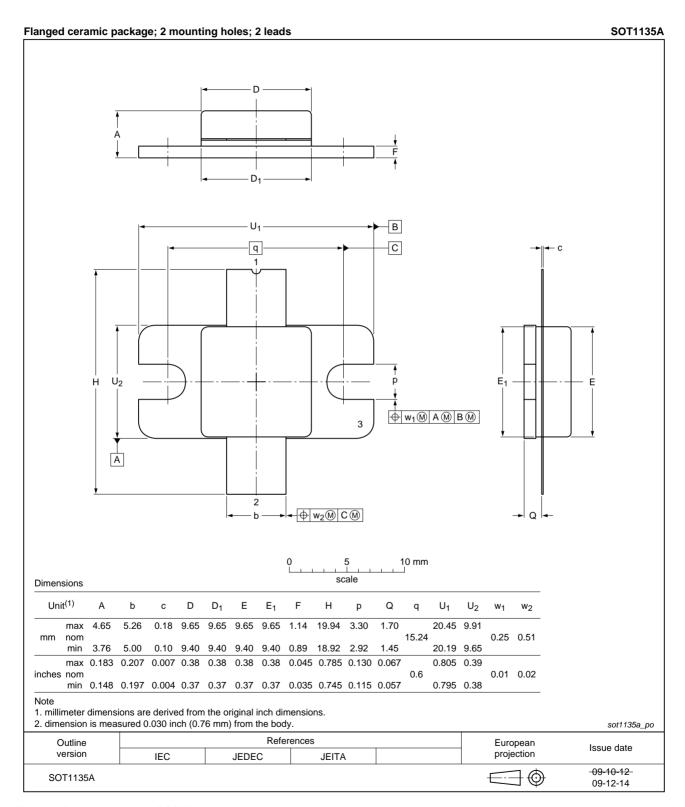


Fig 14. Package outline SOT1135A

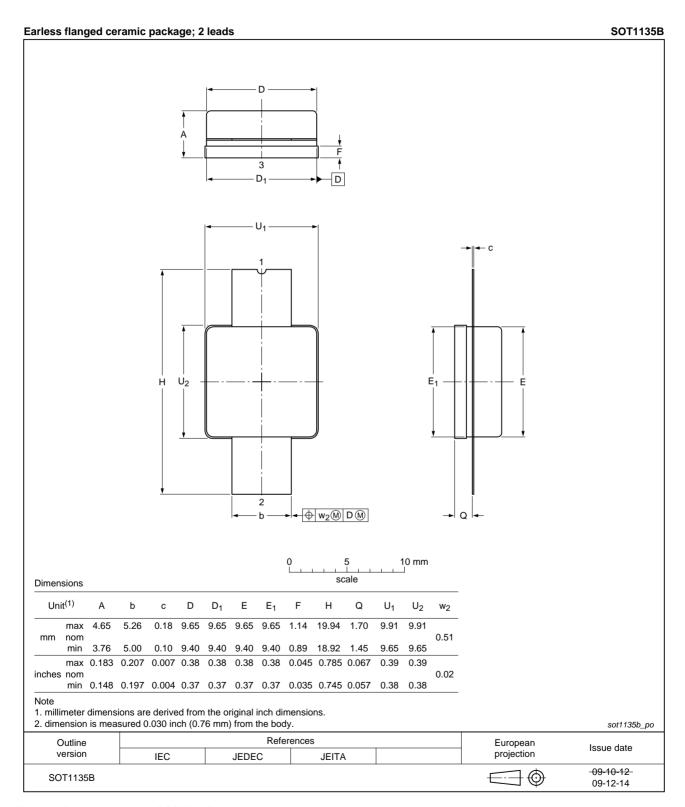


Fig 15. Package outline SOT1135B

BLS6G2735L-30_6G2735LS-30#4

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10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

11. Abbreviations

Table 11. Abbreviations

Acronym	Description
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
S-band	Short wave Band
VSWR	Voltage Standing-Wave Ratio

12. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BLS6G2735L-30_6G2735LS-30#4	20150901	Product data sheet		BLS6G2735L-30_6G 2735LS-30 v.3		
Modifications:	 The format of this document has been redesigned to comply with the new ide guidelines of Ampleon. 					
	 Legal texts h 	ave been adapted to the r	new company name	where appropriate.		
BLS6G2735L-30_6G2735LS-30 v.3	20120924	Product data sheet	-	BLS6G2735L-30_ 6G2735LS-30 v.2		
BLS6G2735L-30_6G2735LS-30 v.2	20120904	Preliminary data sheet	-	BLS6G2735L-30_ 6G2735LS-30 v.1		
BLS6G2735L-30_6G2735LS-30 v.1	20111011	Objective data sheet	-	-		

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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S-band LDMOS transistor

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S-band LDMOS transistor

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